

Description

The SM2320NSAC-TRG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = 20V I_D =6 A

 $R_{DS(ON)} < 27m\Omega @ V_{GS}=4.5V$

Application

Battery protection

Load switch Uninterruptible power supply

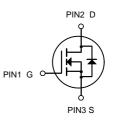
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SM2320NSAC-TRG	SOT23-3L	AE9T	3000

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Limit	Unit	
Vds	Drain-Source Voltage		20	V	
Vgs	Gate-Source Voltage		±12	V	
		T _A =25℃	6	_	
ID	Continuous Drain Current	T _A =70 ℃	3.6	A	
DM	Drain Current-Pulsed (Note 1)		15	А	
PD	Maximum Power Dissipation		1.25	W	
TJ,Tstg	Operating Junction and Storage Temperature Range		-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		100	°C /W	





N-Channel MOSFET



SM2320NSAC-TRG

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	22.5	-	V
Zero Gate Voltage Drain Current	ldss	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.65	1.0	V
		V _{GS} =4.5V, I _D =4.0 A	-	22	27	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =2.5V, I _D =4.5A	-	28	40	mΩ
Forward Transconductance	grs	V _{DS} =10V,I _D =4A	-	10	-	S
Input Capacitance	Clss	V _{DS} =8V,V _{GS} =0V,	-	500	-	PF
Output Capacitance	Coss		-	295	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	96	-	PF
Turn-on Delay Time	td(on)	V _{DD} =10V,I _D =1A V _{GS} =4.5V,R _{GEN} =6Ω	-	11	-	nS
Turn-on Rise Time	tr		-	30	-	nS
Turn-Off Delay Time	td(off)		-	35	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =3A,V _{GS} =4.5V	-	10	15	nC
Gate-Source Charge	Q _{gs}		-	2.3	-	nC
Gate-Drain Charge	Q _{gd}		-	2.9	-	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4.5	Α

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.

2. Surface mounted on FR4 Board, t \leq 10 sec.

3. Pulse test: pulse width \leq 300µs, duty cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

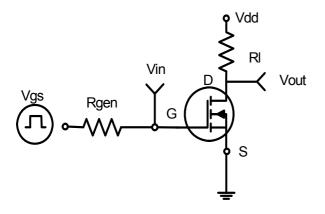


Figure 1:Switching Test Circuit

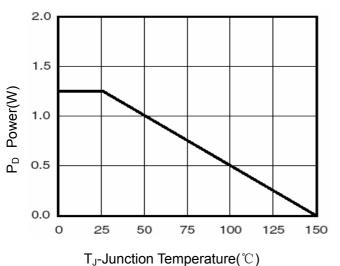
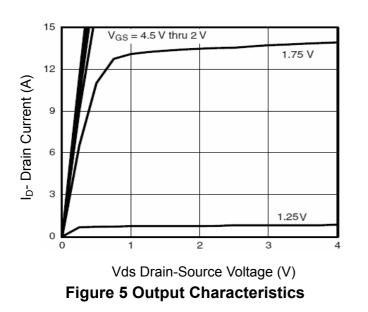


Figure 3 Power Dissipation



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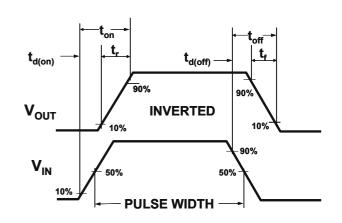
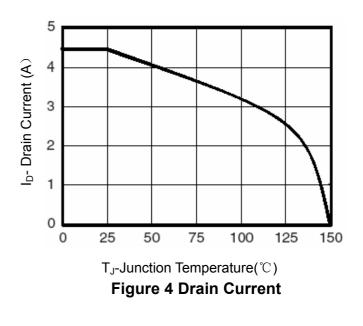
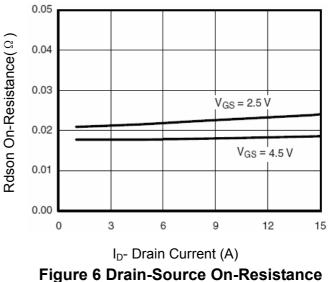
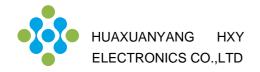


Figure 2:Switching Waveforms

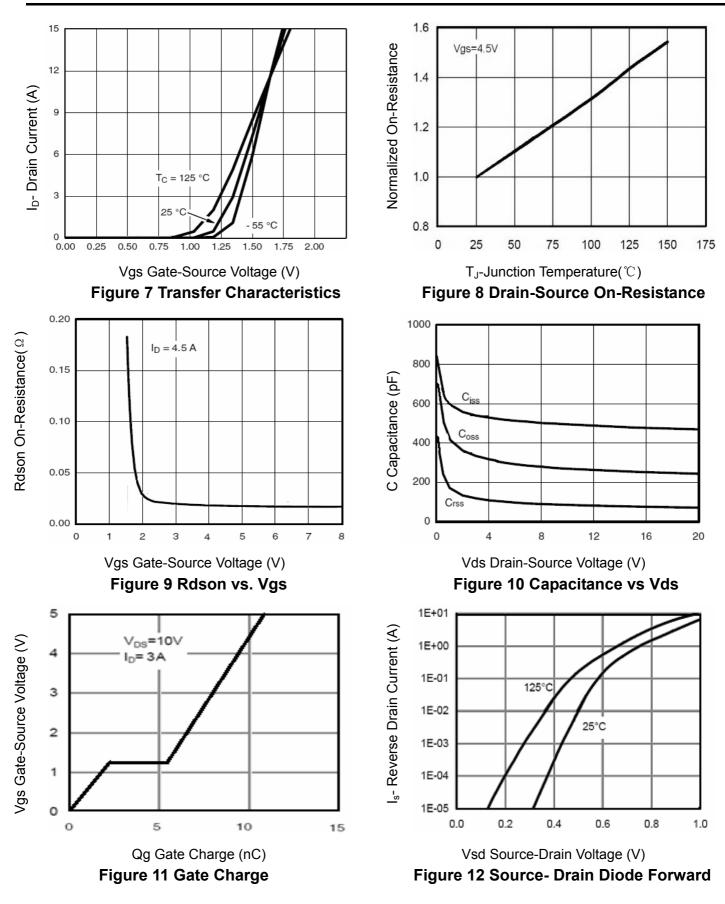


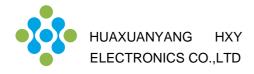




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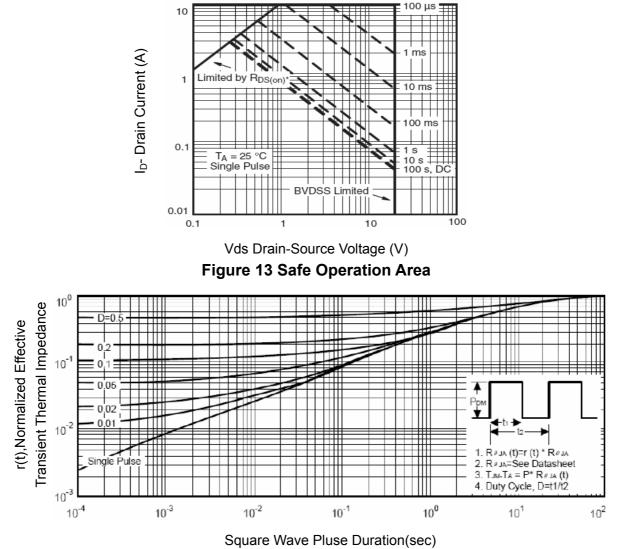
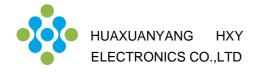
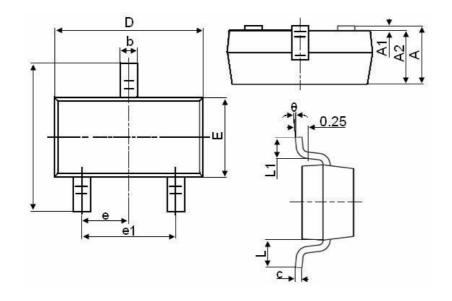


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
A	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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